

# Enhancement Mode N-Channel Power MOSFET

## Features

- ◆ Low  $R_{DS(on)}$  & FOM
- ◆ Excellent low switching loss
- ◆ Excellent stability and uniformity
- ◆ Easy to drive

## Applications

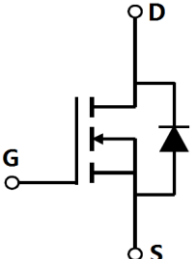
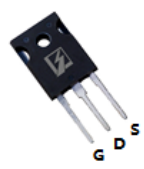
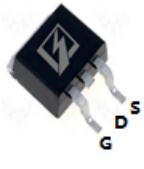
- ◆ PC power
- ◆ Server power supply
- ◆ Telecom
- ◆ Solar inverter
- ◆ Super charger for automobiles

## ■ General Description

OSG65R125xF use advanced GreenMOST™ technology to provide low  $R_{DS(ON)}$ , low gate charge, fast switching and excellent avalanche characteristics. This device is suitable for telecom and super charger applications.

◆ $V_{DS, min@Tjmax}$	700 V
◆ $I_{D, pulse}$	75 A
◆ $R_{DS(ON), max @ V_{GS}=10 V}$	125 mΩ
◆ $Q_g$	41.9 nC

## ■ Schematic and Package Information

SCHEMATIC DIAGRAM	PIN ASSIGNMENT-TOP VIEW
	<div style="display: flex; justify-content: space-around;"> <div data-bbox="933 750 1109 1064">  <p><b>TO247</b> <b>OSG65R125HF</b></p> </div> <div data-bbox="1165 750 1340 1064">  <p><b>TO263</b> <b>OSG65R125KF</b></p> </div> </div>

## ■ Absolute Maximum Ratings at $T_j=25^{\circ}\text{C}$ unless otherwise noted

PARAMETER	SYMBOL	VALUE	UNIT
Drain source voltage	$V_{DS}$	650	V
Gate source voltage	$V_{GS}$	±30	V
Continuous drain current <sup>1)</sup> , $T_C=25^{\circ}\text{C}$	$I_D$	25	A
Continuous drain current <sup>1)</sup> , $T_C=100^{\circ}\text{C}$		16	
Pulsed drain current <sup>2)</sup> , $T_C=25^{\circ}\text{C}$	$I_{D, pulse}$	75	A
Power dissipation <sup>3)</sup> , $T_C=25^{\circ}\text{C}$	$P_D$	101	W
Single pulsed avalanche energy <sup>5)</sup>	$E_{AS}$	774	mJ
MOSFET dv/dt ruggedness, $V_{DS}=0\text{...}480\text{ V}$	dv/dt	50	V/ns
Reverse diode dv/dt, $V_{DS}=0\text{...}480\text{ V}$ , $I_{SD}\leq I_D$	dv/dt	15	V/ns
Operation and storage temperature	$T_{stg}, T_j$	-55 to 150	°C

## ■ Thermal Characteristics

PARAMETER	SYMBOL	VALUE	UNIT
Thermal resistance, junction-case	$R_{\theta JC}$	1.24	°C/W
Thermal resistance, junction-ambient <sup>4)</sup>	$R_{\theta JA}$	62.5	°C/W

## ■ Electrical Characteristics at $T_j=25\text{ }^\circ\text{C}$ unless otherwise specified

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
Drain-source breakdown voltage	$BV_{DSS}$	650			V	$V_{GS}=0\text{ V}$ , $I_D=1\text{ mA}$
		700	740			$V_{GS}=0\text{ V}$ , $I_D=1\text{ mA}$ , $T_j=150\text{ }^\circ\text{C}$
Gate threshold voltage	$V_{GS(th)}$	2.9		3.9	V	$V_{DS}=V_{GS}$ , $I_D=1\text{ mA}$
Drain-source on-state resistance	$R_{DS(on)}$		0.115	0.125	$\Omega$	$V_{GS}=10\text{ V}$ , $I_D=12.5\text{ A}$
			0.278			$V_{GS}=10\text{ V}$ , $I_D=12.5\text{ A}$ , $T_j=150\text{ }^\circ\text{C}$
Gate-source leakage current	$I_{GSS}$			100	nA	$V_{GS}=30\text{ V}$
				-100		$V_{GS}=-30\text{ V}$
Drain-source leakage current	$I_{DSS}$			1	$\mu\text{A}$	$V_{DS}=650\text{ V}$ , $V_{GS}=0\text{ V}$

## ■ Dynamic Characteristics

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
Input capacitance	$C_{iss}$		2390.8		pF	$V_{GS}=0\text{ V}$ , $V_{DS}=50\text{ V}$ , $f=100\text{ kHz}$
Output capacitance	$C_{oss}$		154.1		pF	
Reverse transfer capacitance	$C_{rss}$		3.9		pF	
Turn-on delay time	$t_{d(on)}$		32.4		ns	$V_{GS}=10\text{ V}$ , $V_{DS}=400\text{ V}$ , $R_G=2\text{ }\Omega$ , $I_D=12.5\text{ A}$
Rise time	$t_r$		30.8		ns	
Turn-off delay time	$t_{d(off)}$		63.2		ns	
Fall time	$t_f$		4.9		ns	

## ■ Gate Charge Characteristics

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
Total gate charge	$Q_g$		41.9		nC	$I_D=12.5\text{ A}$ , $V_{DS}=400\text{ V}$ , $V_{GS}=10\text{ V}$
Gate-source charge	$Q_{gs}$		10.4		nC	
Gate-drain charge	$Q_{gd}$		14.1		nC	
Gate plateau voltage	$V_{\text{plateau}}$		5.7		V	

## ■ Body Diode Characteristics

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
Diode forward current	$I_S$			25	A	$V_{GS} < V_{th}$
Pulsed source current	$I_{SP}$			75		
Diode forward voltage	$V_{SD}$			1.4	V	$I_S=25\text{ A}$ , $V_{GS}=0\text{ V}$
Reverse recovery time	$t_{rr}$		365.2		ns	$V_R=400\text{ V}$ , $I_S=12.5\text{ A}$ , $di/dt=100\text{ A}/\mu\text{s}$
Reverse recovery charge	$Q_{rr}$		4.7		$\mu\text{C}$	
Peak reverse recovery current	$I_{rrm}$		24.9		A	

## ■ Note

- 1) Calculated continuous current based on maximum allowable junction temperature.
- 2) Repetitive rating; pulse width limited by max. junction temperature.
- 3)  $P_d$  is based on max. junction temperature, using junction-case thermal resistance.
- 4) The value of  $R_{\theta JA}$  is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with  $T_a=25\text{ }^\circ\text{C}$ .
- 5)  $V_{DD}=100\text{ V}$ ,  $R_G=25\text{ }\Omega$ ,  $L=80\text{ mH}$ , starting  $T_j=25\text{ }^\circ\text{C}$ .

■ **Electrical Characteristics Diagrams**

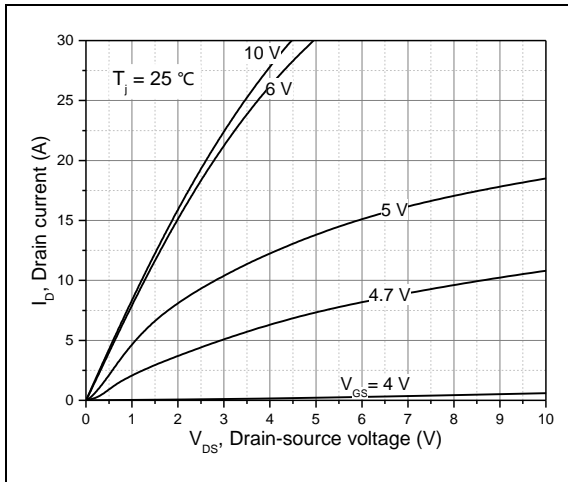


Figure 1, Typ. output characteristics

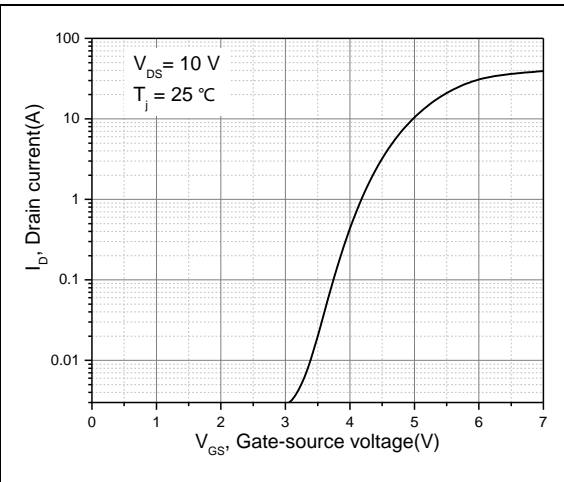


Figure 2, Typ. transfer characteristics

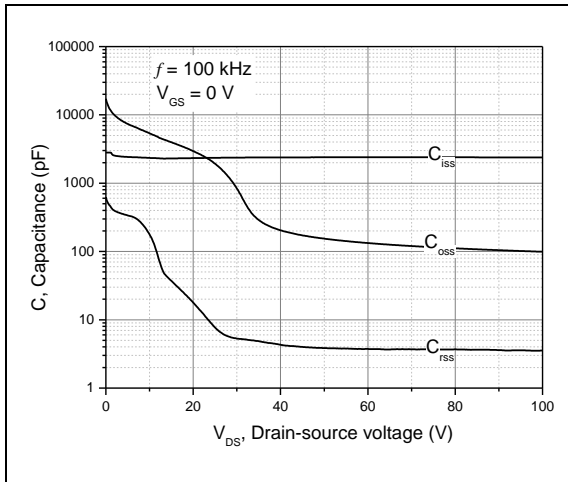


Figure 3, Typ. capacitances

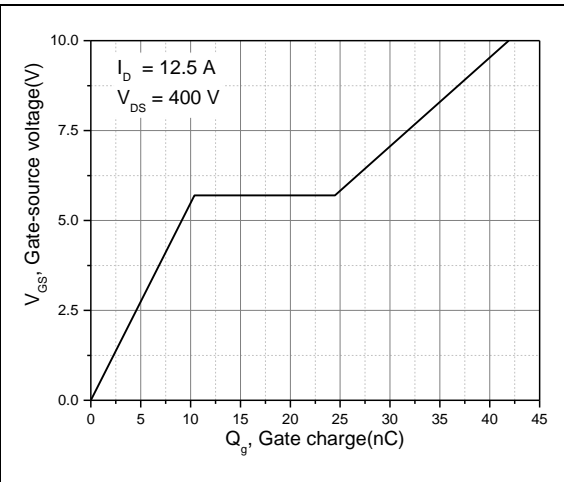


Figure 4, Typ. gate charge

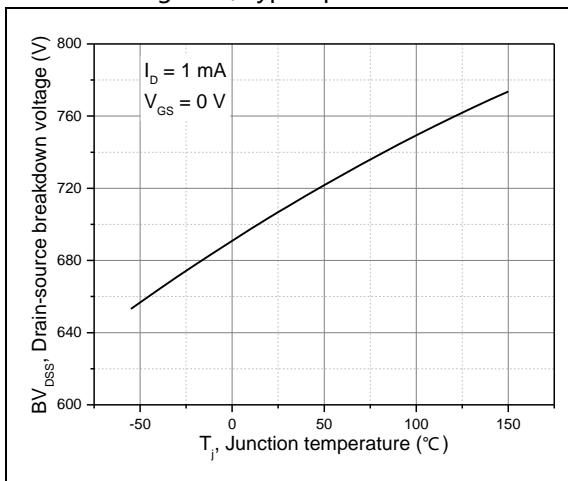


Figure 5, Drain-source breakdown voltage

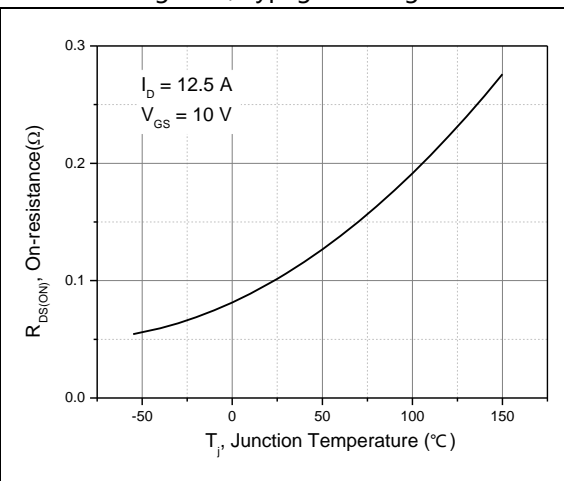


Figure 6, Drain-source on-state resistance

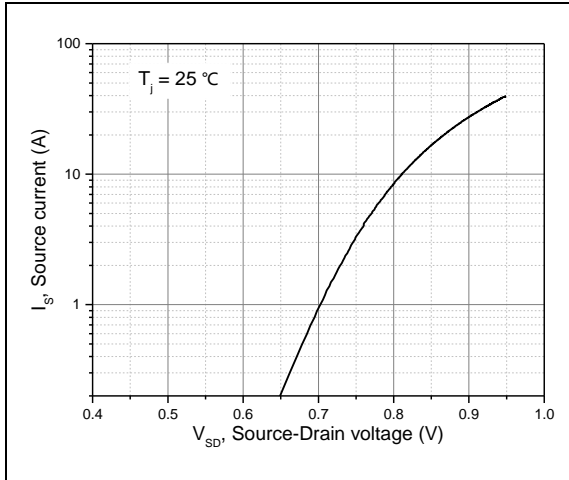


Figure 7, Forward characteristic of body diode

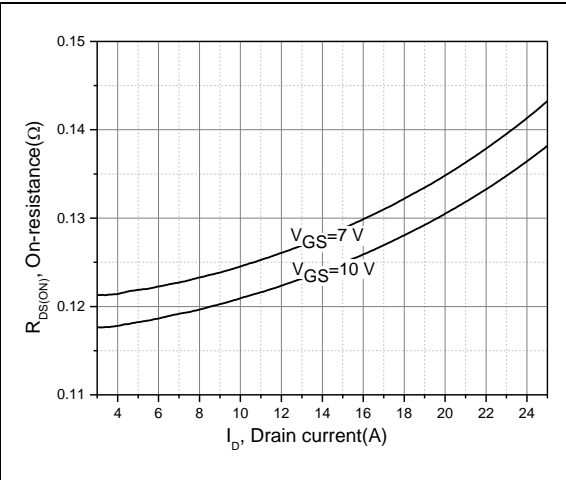


Figure 8, Drain-source on-state resistance

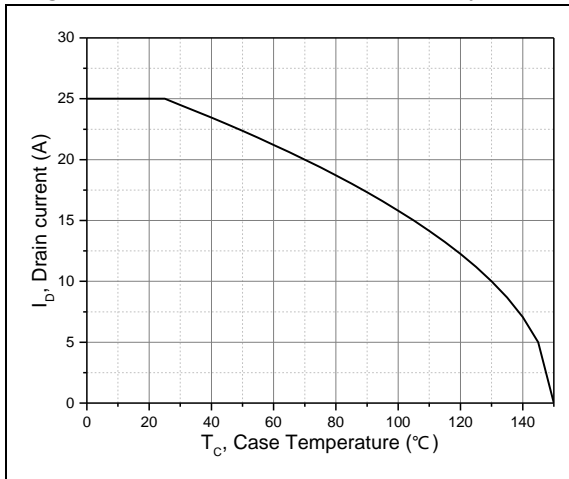


Figure 9, Drain current

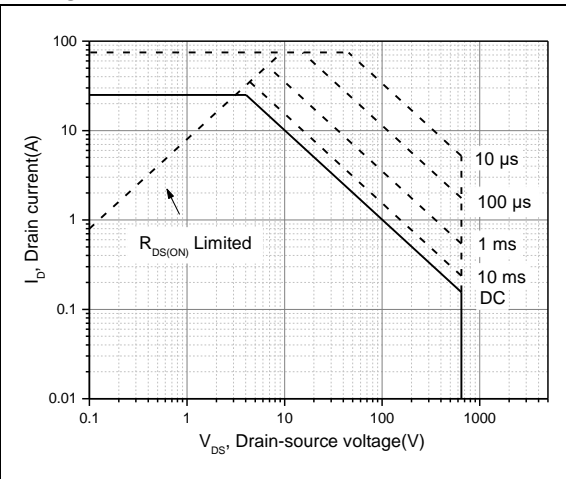


Figure 10, Safe operation area  $T_C = 25\text{ °C}$

■ Test circuits and waveforms

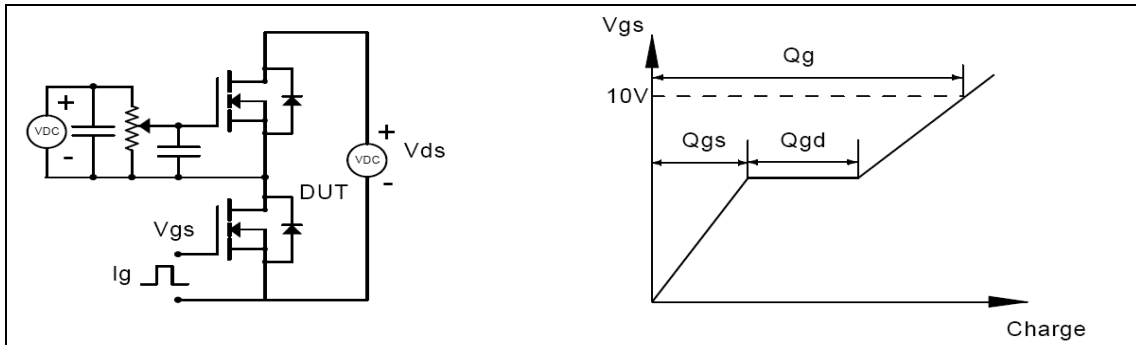


Figure 1, Gate charge test circuit & waveform

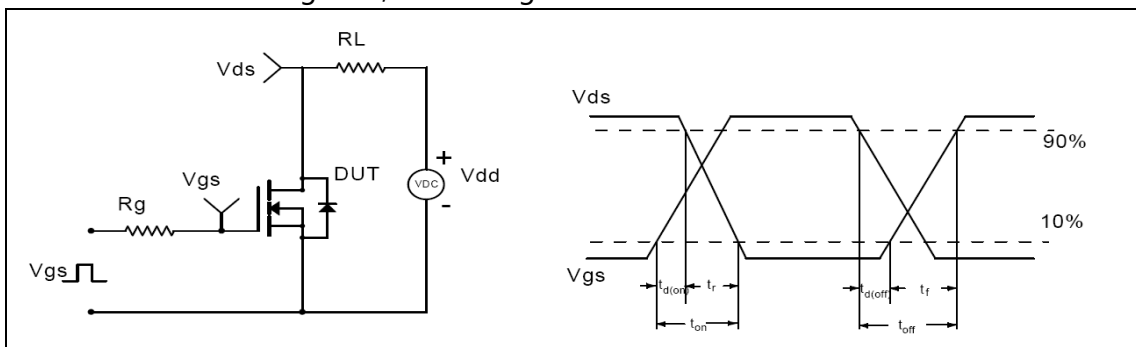


Figure 2, Switching time test circuit & waveforms

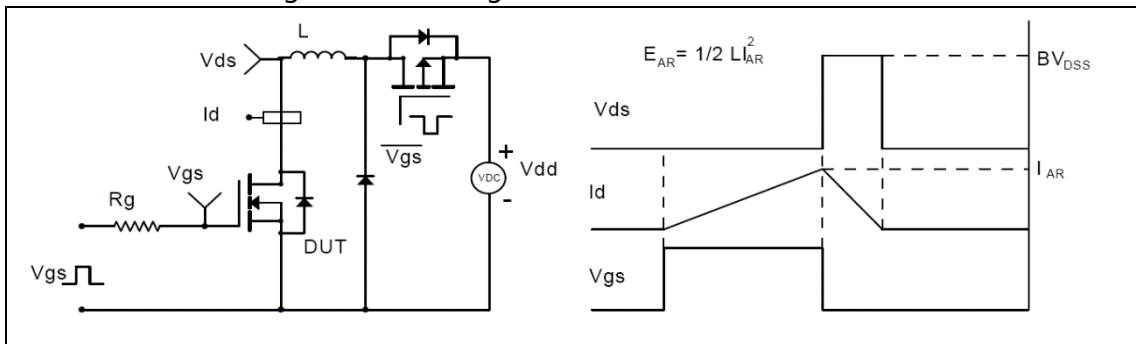


Figure 3, Unclamped inductive switching (UIS) test circuit & waveforms

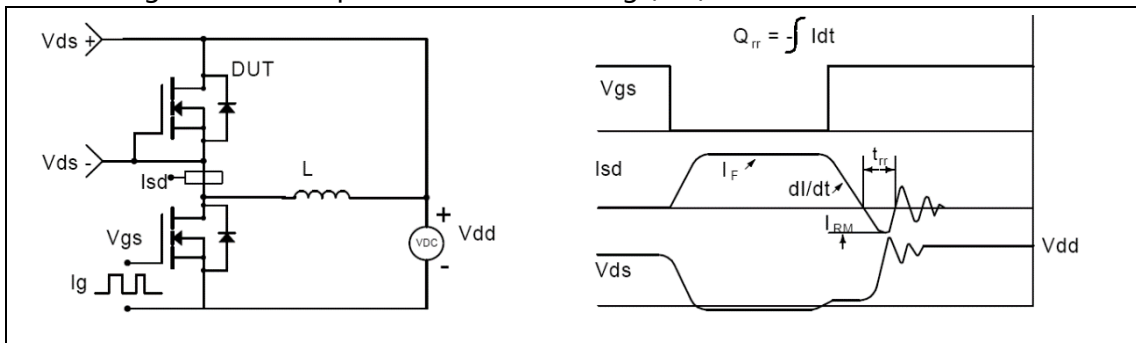
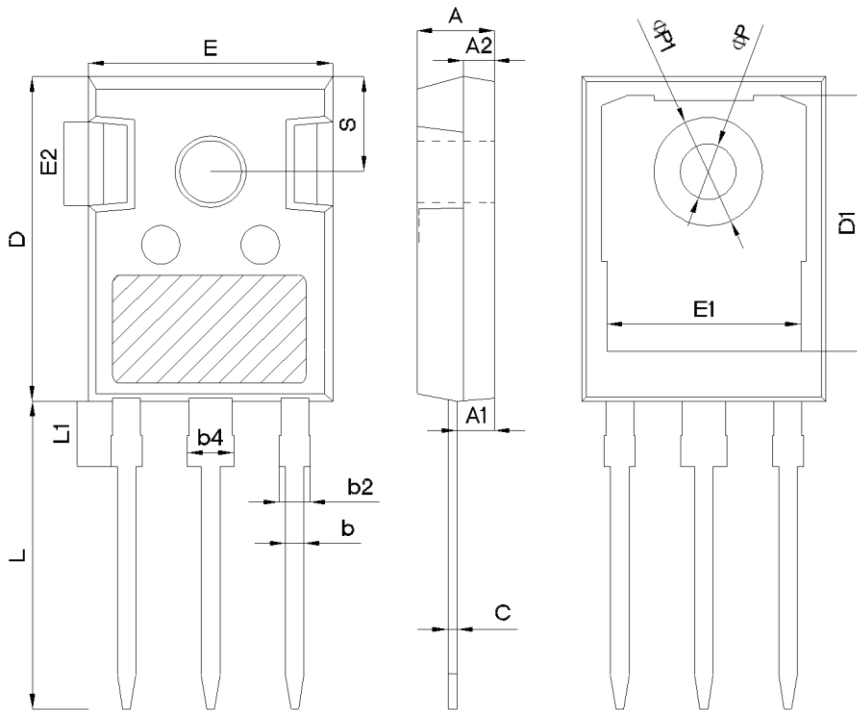


Figure 4, Diode reverse recovery test circuit & waveforms

**■ Package Information**

Figure1, TO247 package outline dimension

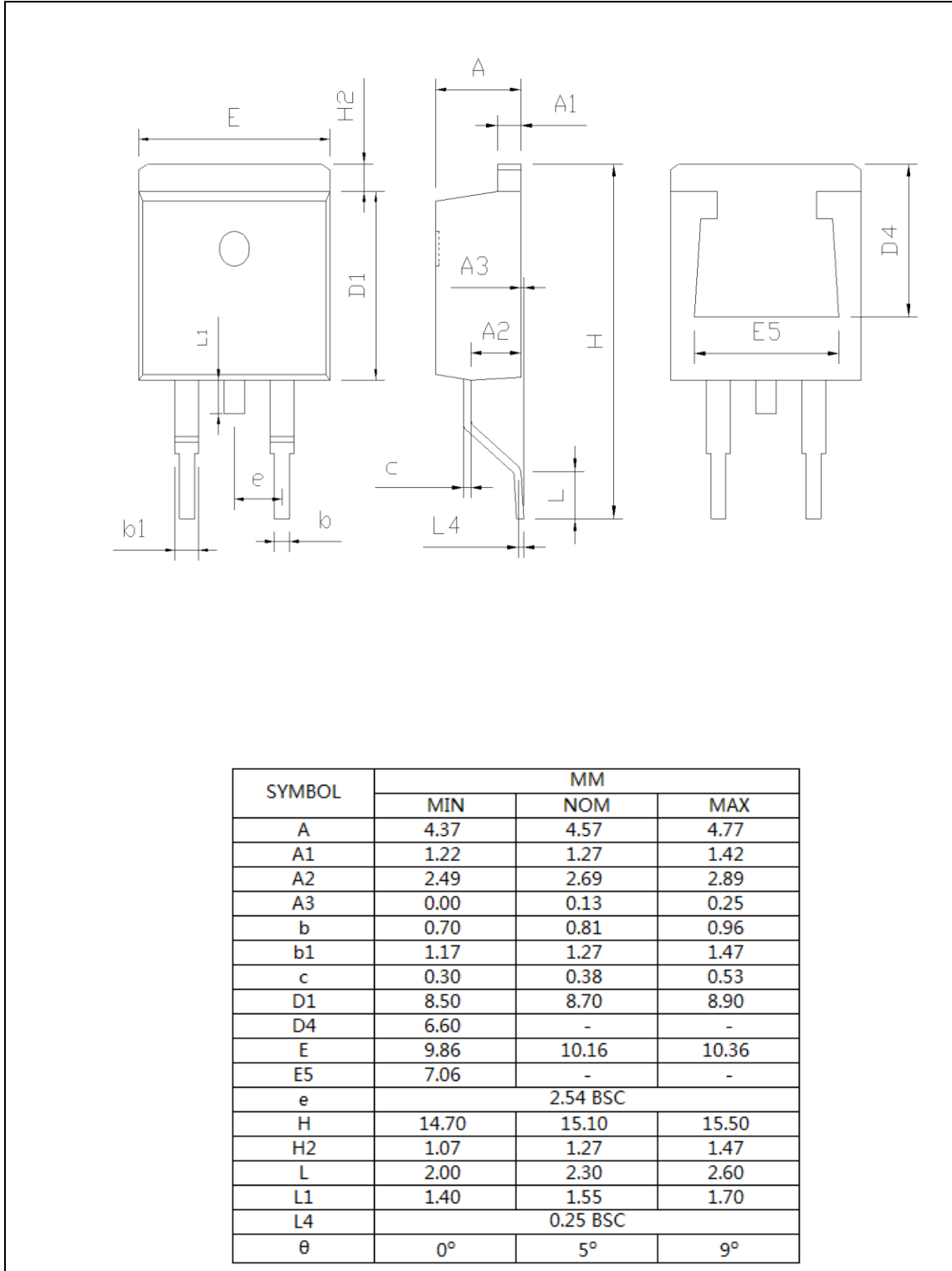


SYMBOL	mm		
	MIN	NOM	MAX
A	4.80	5.00	5.20
A1	2.21	2.41	2.61
A2	1.85	2.00	2.15
b	1.11	1.21	1.36
b2	1.91	2.01	2.21
b4	2.91	3.01	3.21
c	0.51	0.61	0.75
D	20.70	21.00	21.30
D1	16.25	16.55	16.85
E	15.50	15.80	16.10
E1	13.00	13.30	13.60
E2	4.80	5.00	5.20
E3	2.30	2.50	2.70
e	5.44BSC		
L	19.62	19.92	20.22
L1	-	-	4.30
ΦP	3.40	3.60	3.80
ΦP1	-	-	7.30
S	6.15BSC		



**■ Package Information**

Figure2, TO263 package outline dimension



## ■ Ordering Information

Package	Units/Tube	Tapes/Inner Box	Units/Inner Box	Inner Box/Carton Box	Units/Carton Box
TO247	30	11	330	6	1980
TO263 <sup>Option1</sup>	50	20	1000	6	6000

Package	Units/Tape	Tapes/Inner Box	Units/Inner Box	Inner Box/Carton Box	Units/Carton Box
TO263 <sup>Option2</sup>	800	1	800	5	4000

## ■ Product Information

Product	Package	Pb Free	RoHS	Halogen Free
OSG65R125HF	TO247	yes	yes	yes
OSG65R125KF	TO263	yes	yes	yes